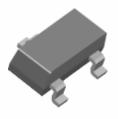
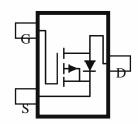
### P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize High Cell Density process. Low  $r_{DS(on)}$  assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are DC-DC converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- $\begin{array}{ll} \bullet & \quad \text{Low } r_{DS(on)} \, \text{Provides Higher Efficiency and} \\ \text{Extends Battery Life} \\ \end{array}$
- Miniature SOT-23 Surface Mount Package Saves Board Space
- · Fast switching speed
- High performance trench technology

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)}$ (OHM)	$I_{D}(A)$		
	$0.052$ @ $V_{GS} = -4.5V$	-3.6		
-20	$0.072$ @ $V_{GS} = -2.5V$	-3.1		
	$0.120 @ V_{GS} = -1.8V$	-2.7		





ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)					
Parame te r		Symbol	Ratings	Units	
Drain-Source Voltage			-20	V	
Gate-Source Voltage		$V_{GS}$	±8	V	
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	T.	-3.6		
Continuous Drain Current	$T_A=70^{\circ}C$	ъ	-1.8	A	
Pulsed Drain Current <sup>b</sup>		$I_{DM}$	-10		
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	±0.46	A	
D a	$T_A=25^{\circ}C$	D_	1.25	W	
Power Dissipation <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	Гр	0.8	**	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Maximum	Units	
Manimum Innation to Ambient <sup>a</sup>	t <= 5 sec	D	100	0C/M	
Maximum Junction-to-Ambient <sup>a</sup>	Steady-State	$\kappa_{ m THJA}$	150	°C/W	

#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

SPECIFICATIONS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Devenue Asse	Cl1		Limits			T7 .4	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Thres hold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -250 \text{ uA}$	-0.7				
Gate-Body Leakage	IGSS	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±100	nA	
	Ţ	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1		
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			-10	uA	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-10			A	
		$V_{GS} = -4.5 \text{ V}, I_D = -3.6 \text{ A}$			52		
Drain-Source On-Resistance <sup>A</sup>	IDS(on)	$V_{GS} = -2.5 \text{ V}, I_D = -3.1 \text{ A}$			72	mΩ	
		$V_{GS} = -1.8 \text{ V}, I_{D} = -2.7 \text{ A}$			120		
Forward Tranconductance <sup>A</sup>	g	V = -5 V, I = -1.25 A		12		S	
Diode Forward Voltage	V <sub>SD</sub>	$I_S = -0.46 \text{ A}, V_{GS} = 0 \text{ V}$		-0.60		V	
Dynamic <sup>b</sup>	fs	DS D					
Total Gate Charge	Qg	V <sub>DS</sub> = -5 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -2.4 A		12.0		nC	
Gate-Source Charge	Qgs			2.0			
Gate-Drain Charge	Qgd			2.0			
Input Capacitance	Ciss	P-Channel VDs=-15V, VGs=0V, f=1MHz		1312		pF	
Output Capacitance	Coss			130			
Reverse Transfer Capacitance	Crss			106			
Turn-On Delay Time	td(on)			6.5			
Rise Time	tr	$V_{DD} = -10 \text{ V, IL} = -1 \text{ A,}$ $V_{GEN} = -4.5 \text{ V, R}_{G} = 6 \Omega$		20		ns	
Turn-Off Delay Time	t <sub>d(off)</sub>			31			
Fall-Time	$t_{\mathrm{f}}$			21			

#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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Freescale AO3415/ MC3415A

## Typical Electrical Characteristics

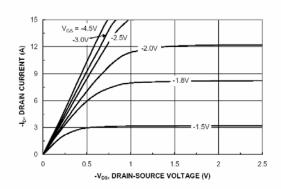


Figure 1. On-Region Characteristics

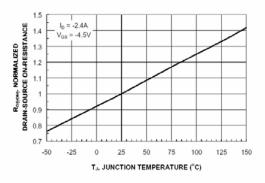


Figure 3. On-Resistance Variation with Temperature

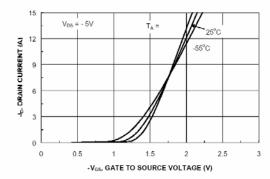


Figure 5. Transfer Characteristics

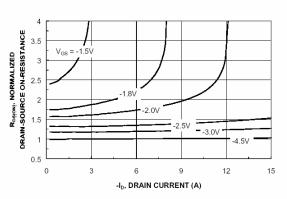


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

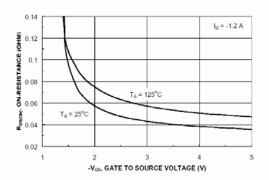


Figure 4. On-Resistance Variation with Gate to Source Voltage

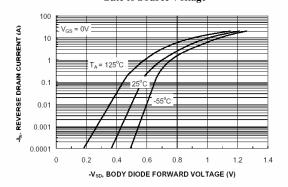
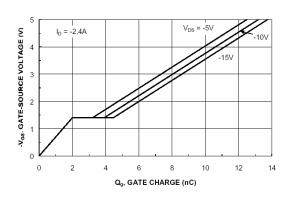


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Freescale AO3415/ MC3415A

## Typical Electrical Characteristics



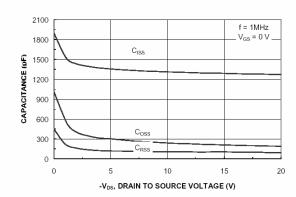


Figure 7. Gate Charge Characteristic

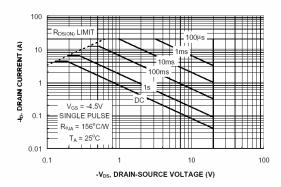


Figure 8. Capacitance Characteristic

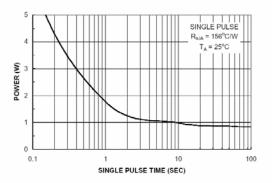


Figure 9. Maximum Safe Operating Area

Figure 10. Single Pulse Maximum Power
Dissipation

#### **Normalized Thermal Transient Junction to Ambient**

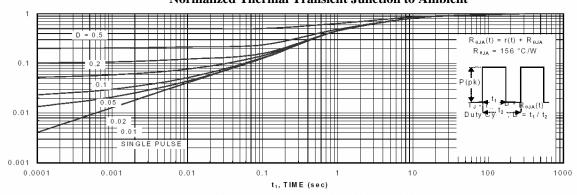
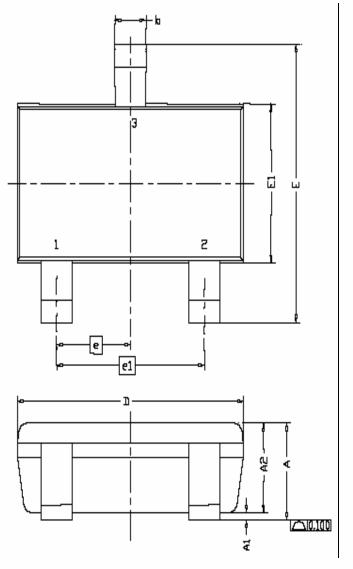
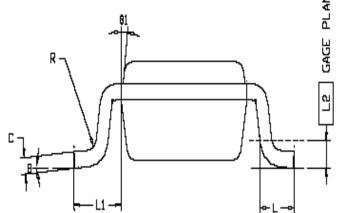


Figure 11. Transient Thermal Response Curve.

# Package Information



пты	MILLIMETERS				
DIM.	MIN	NDM	MAX		
Α	0.935	0.95	1.10		
A1	0.01		0.10		
A2	0.85	0.90	1.925		
р	0.30	0.40	0.50		
С	0.10	0.15	0.25		
D	2.70	2.90	3.10		
Ε	2.60	2.80	3.00		
E1	1.40	1.60	1.80		
6	0.95 BSC				
el	1.90 BSC				
L	0.30	0.40	0.60		
L1	0.60REF				
L2	0.25BSC				
R	0.10				
θ	Q+	4*	8,		
81	7*N□M				



Freescale AO3415/ MC3415A

## Ordering information

AM2327P-T1-XX

A: Analog Power

- M: MOSFET

– 2327: Part number

- P: P-Channel

- T1: Tape & reel

- XX: Blank: Standard

PF: Leadfree